



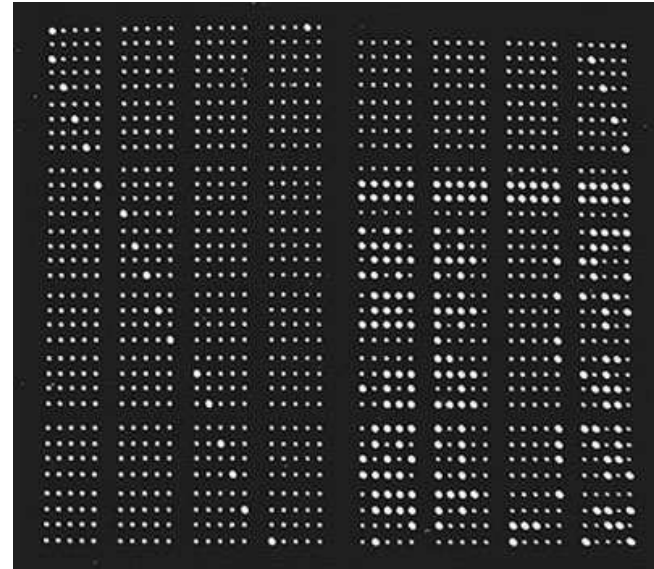
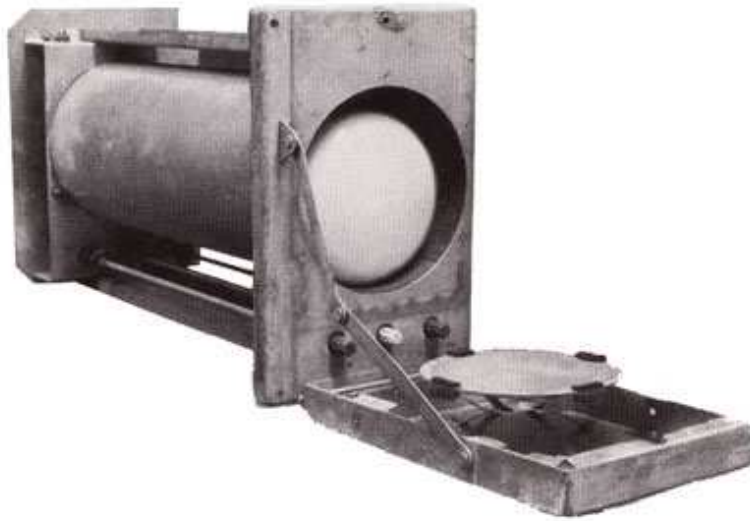
Memory

Prof. Stephen A. Edwards
sedwards@cs.columbia.edu

Columbia University

Spring 2006

Early Memories



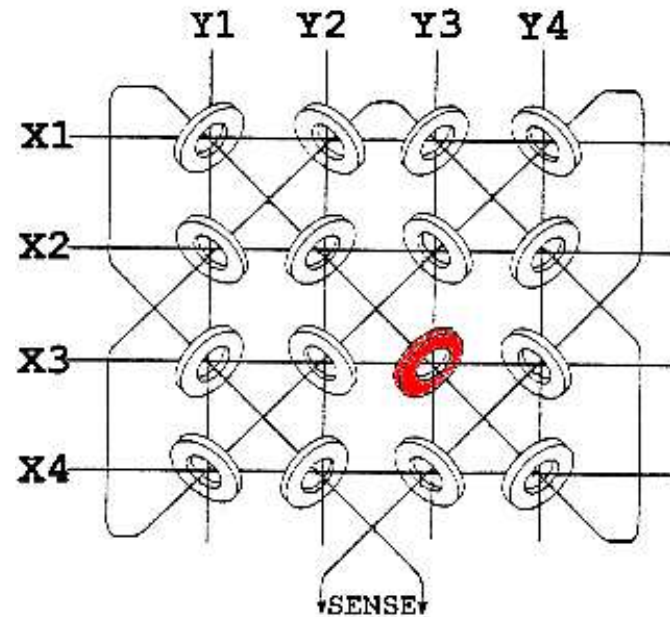
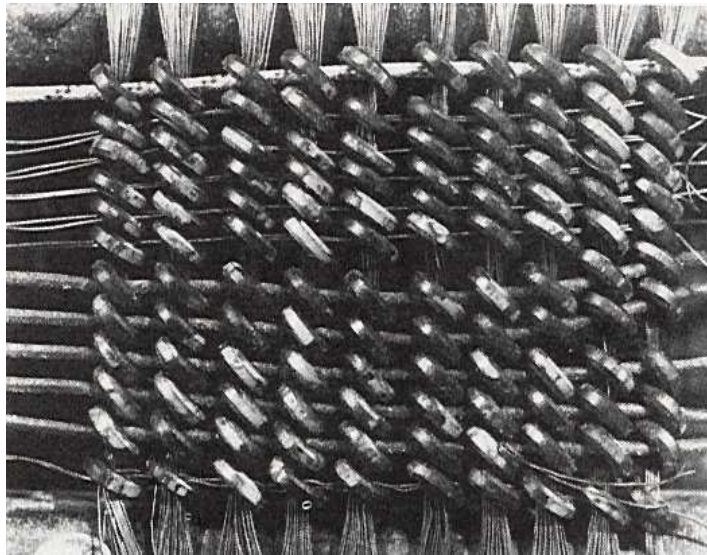
Williams Tube CRT-based random access memory, 1946. Used on the Manchester Mark I. 2048 bits.

Early Memories



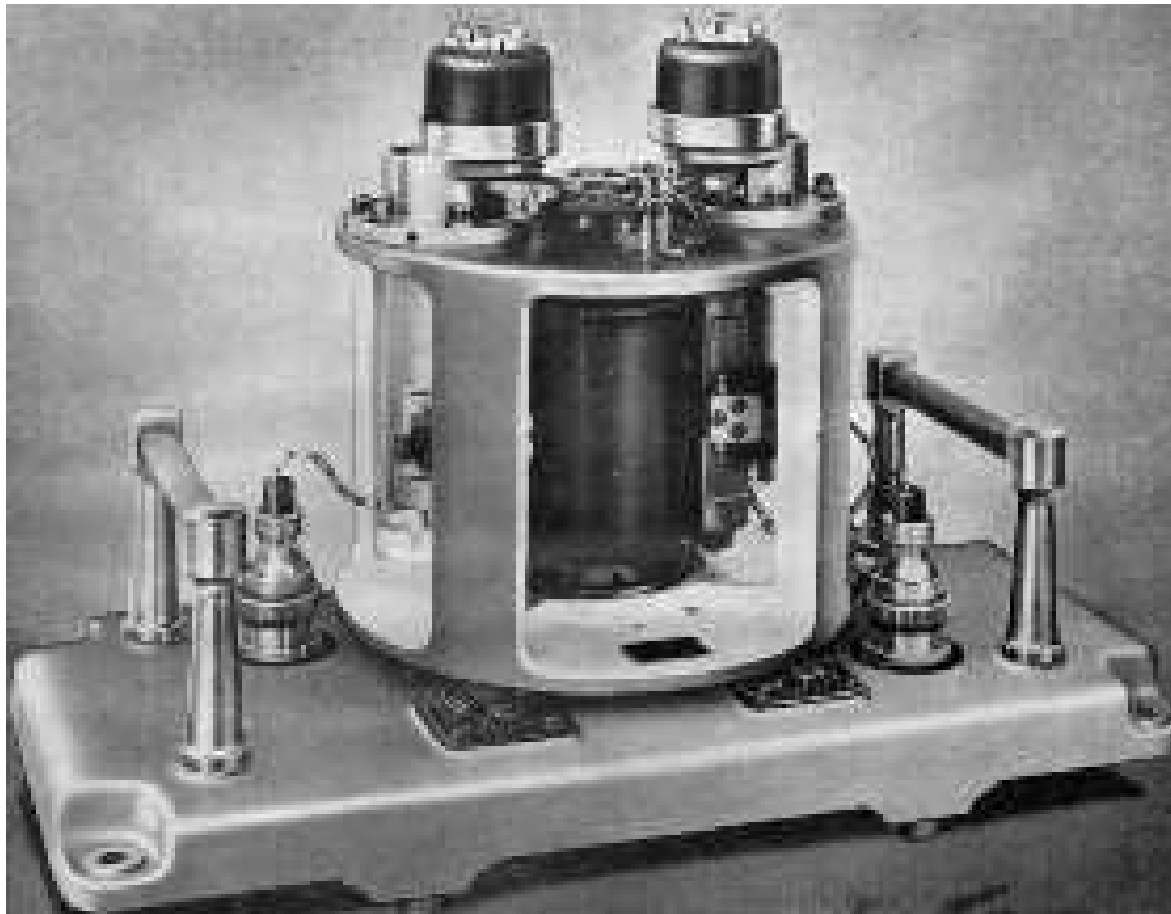
Mercury acoustic
delay line.
Used in the EDASC,
1947.
 32×17 bits

Early Memories



Magnetic core memory, 1952. IBM.

Early Memories



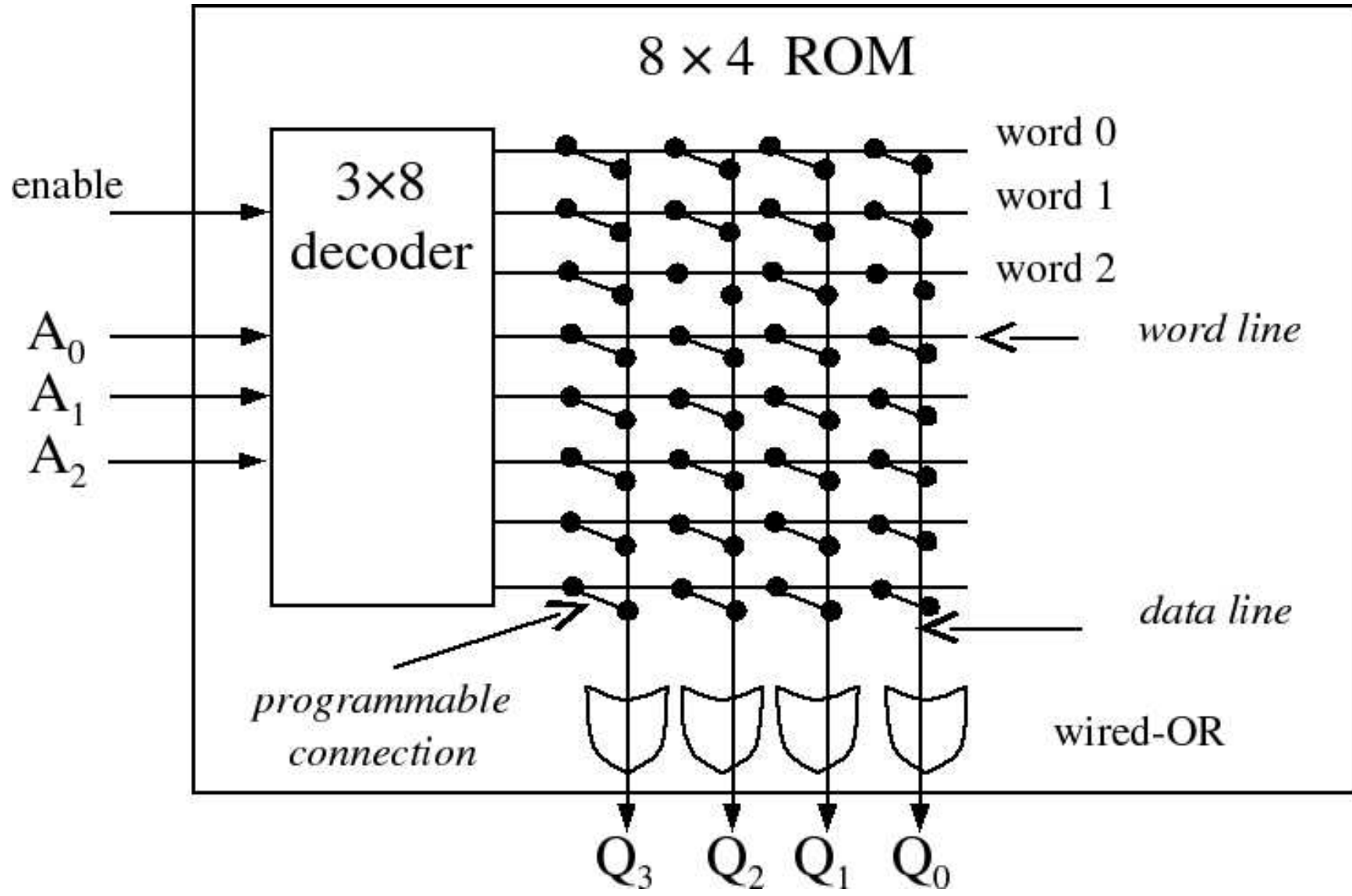
Magnetic drum memory. 1950s & 60s.
Secondary storage.

Modern Memory Choices



Family	Programmed	Persistence
Mask ROM	at fabrication	∞
PROM	once	∞
EPROM	1000s, UV	10 years
FLASH	1000s, block	10 years
EEPROM	1000s, byte	10 years
NVRAM	∞	5 years
SRAM	∞	while powered
DRAM	∞	64 ms

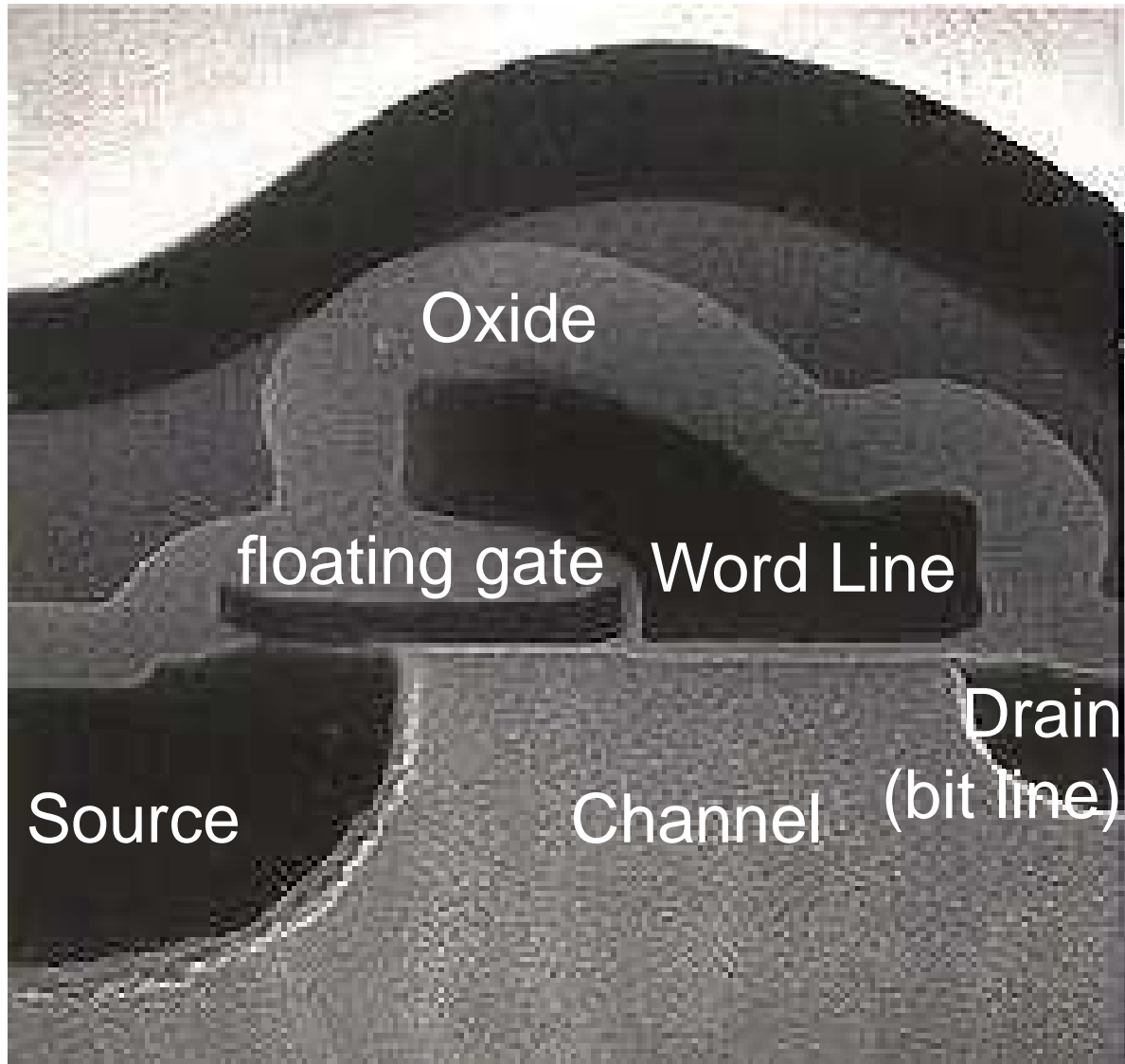
ROMs



EPROMs



EEPROM and FLASH



Slow write

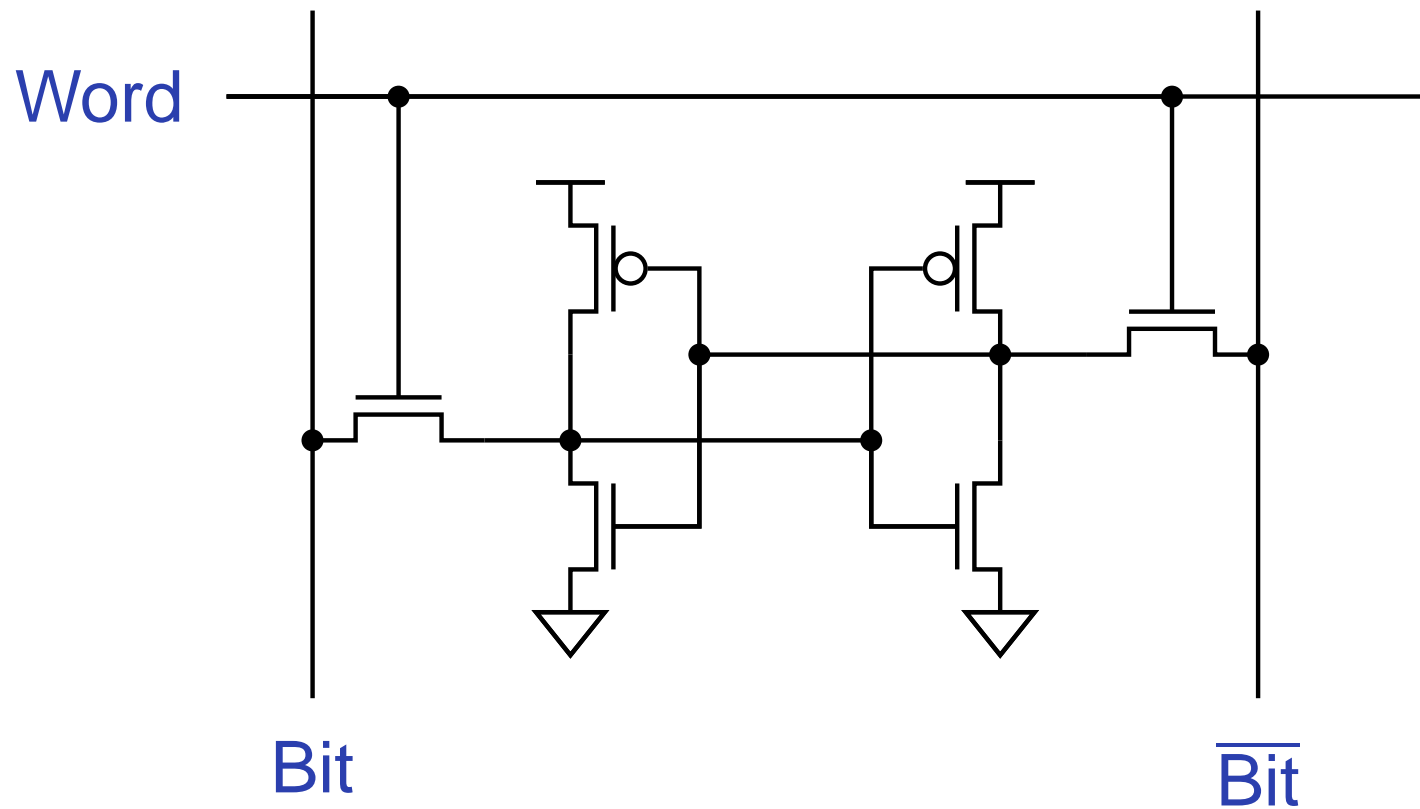
Fowler-
Nordheim
Tunneling

EEPROM: bit
at a time

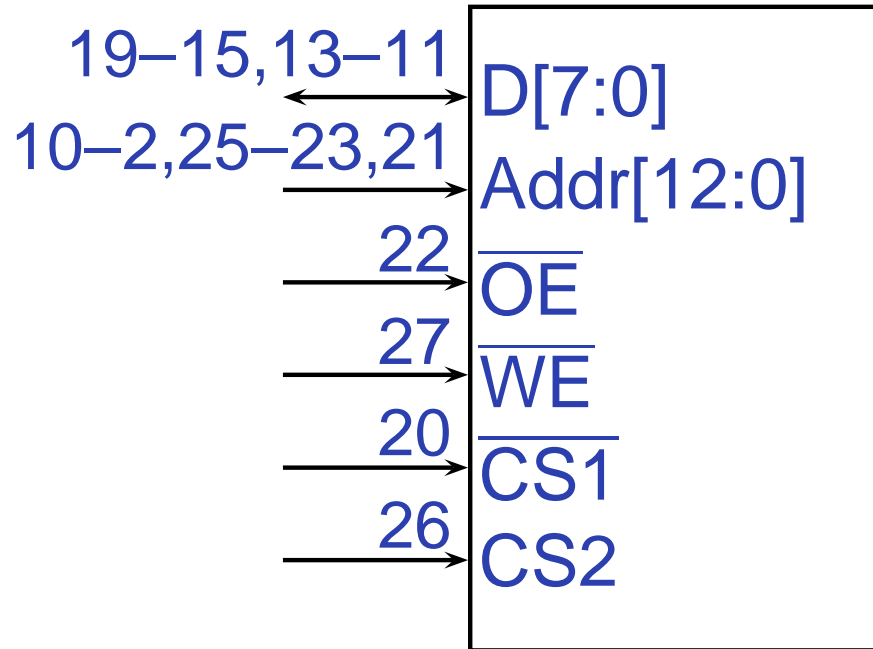
FLASH: block
at a time

Source: SST

Static RAM Cell



Standard SRAM: 6264

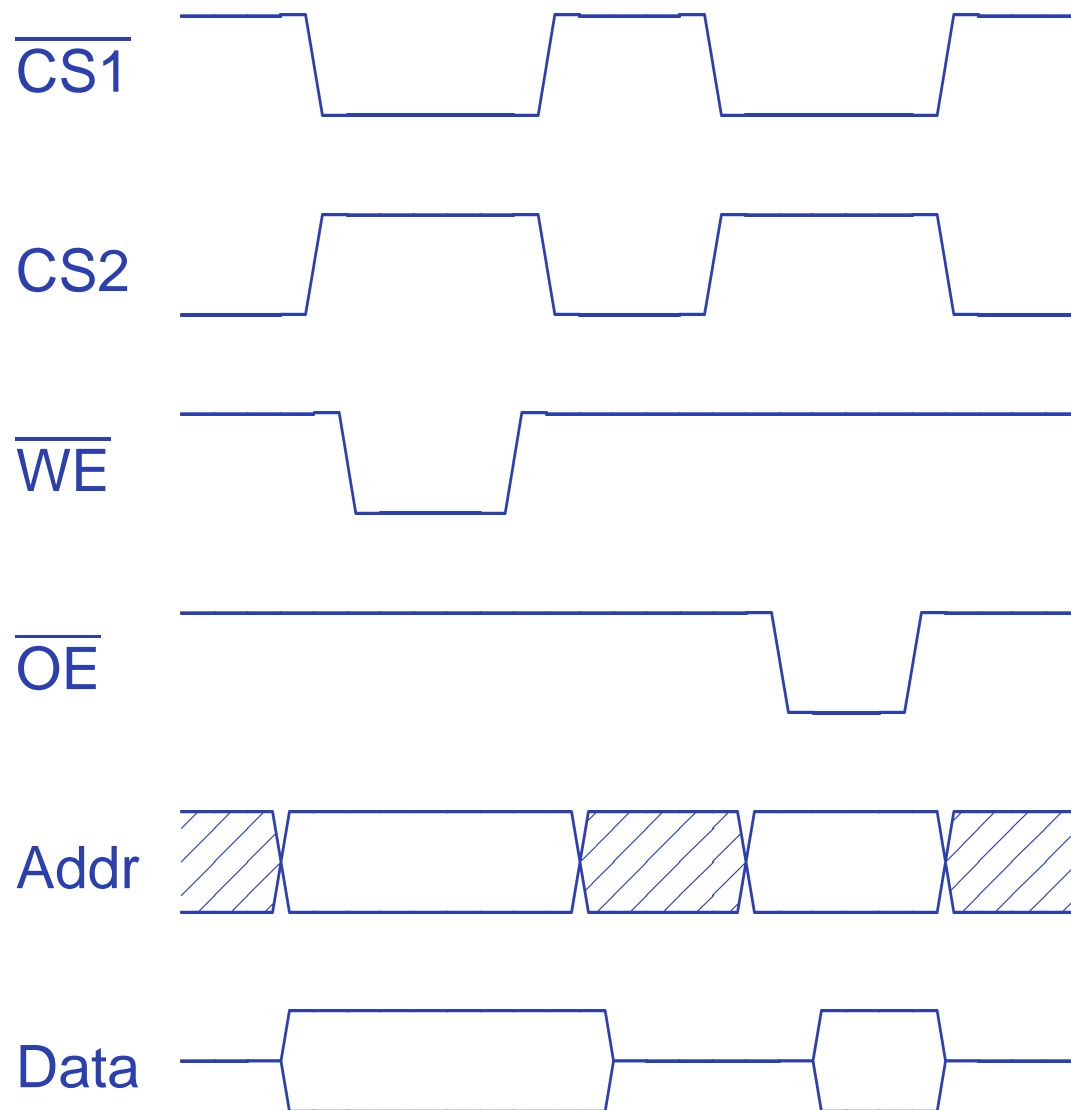


8K × 8

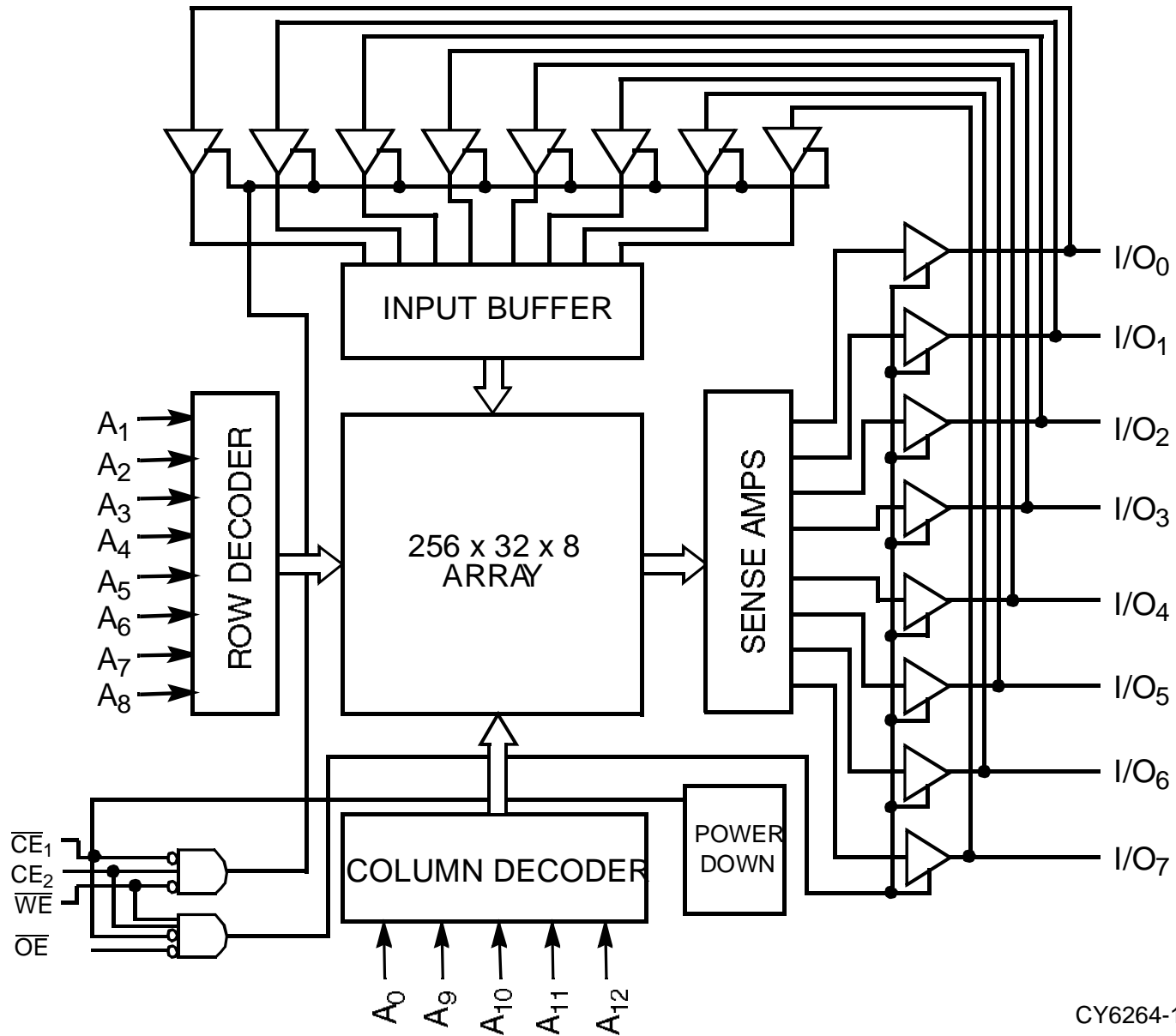
Can be very fast:
Cypress sells a 55ns
version

Simple, asynchronous
interface

Standard SRAM: 6264

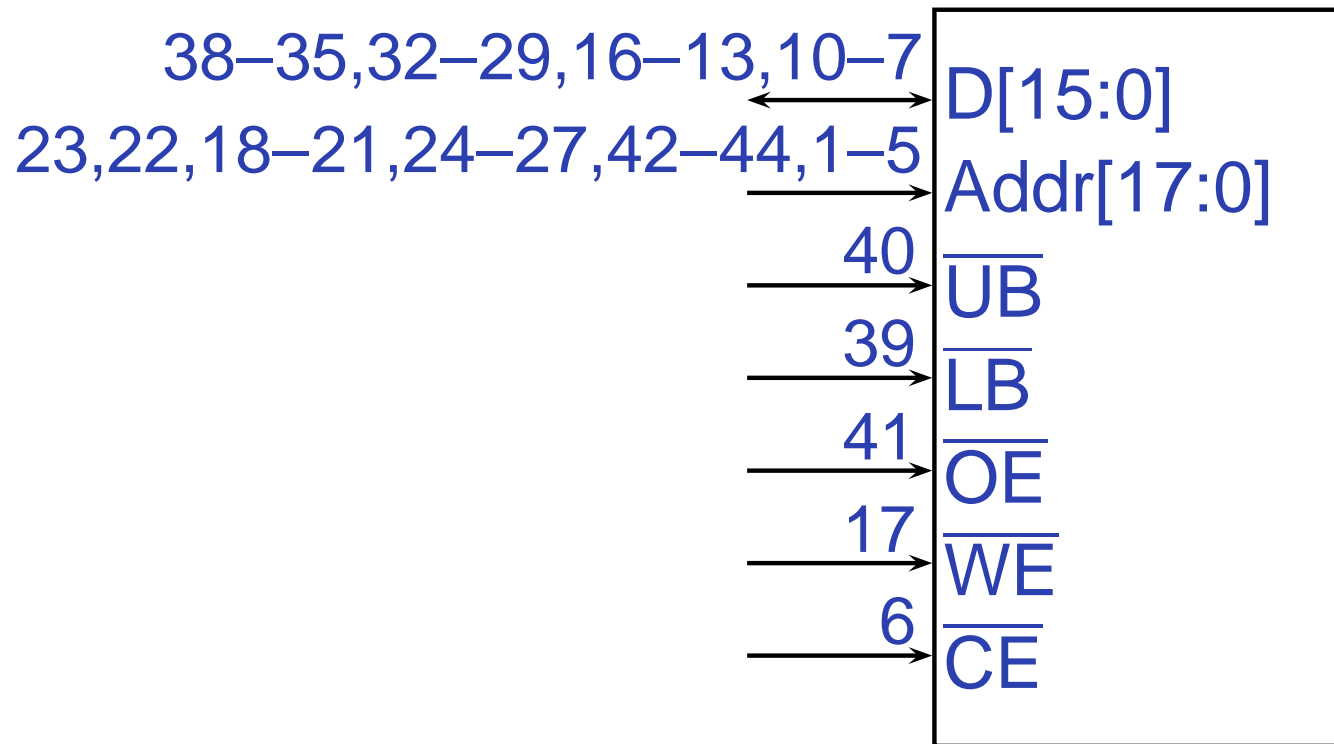


Standard SRAM: 6264



CY6264-1

Toshiba TC55V16256J 256K × 16

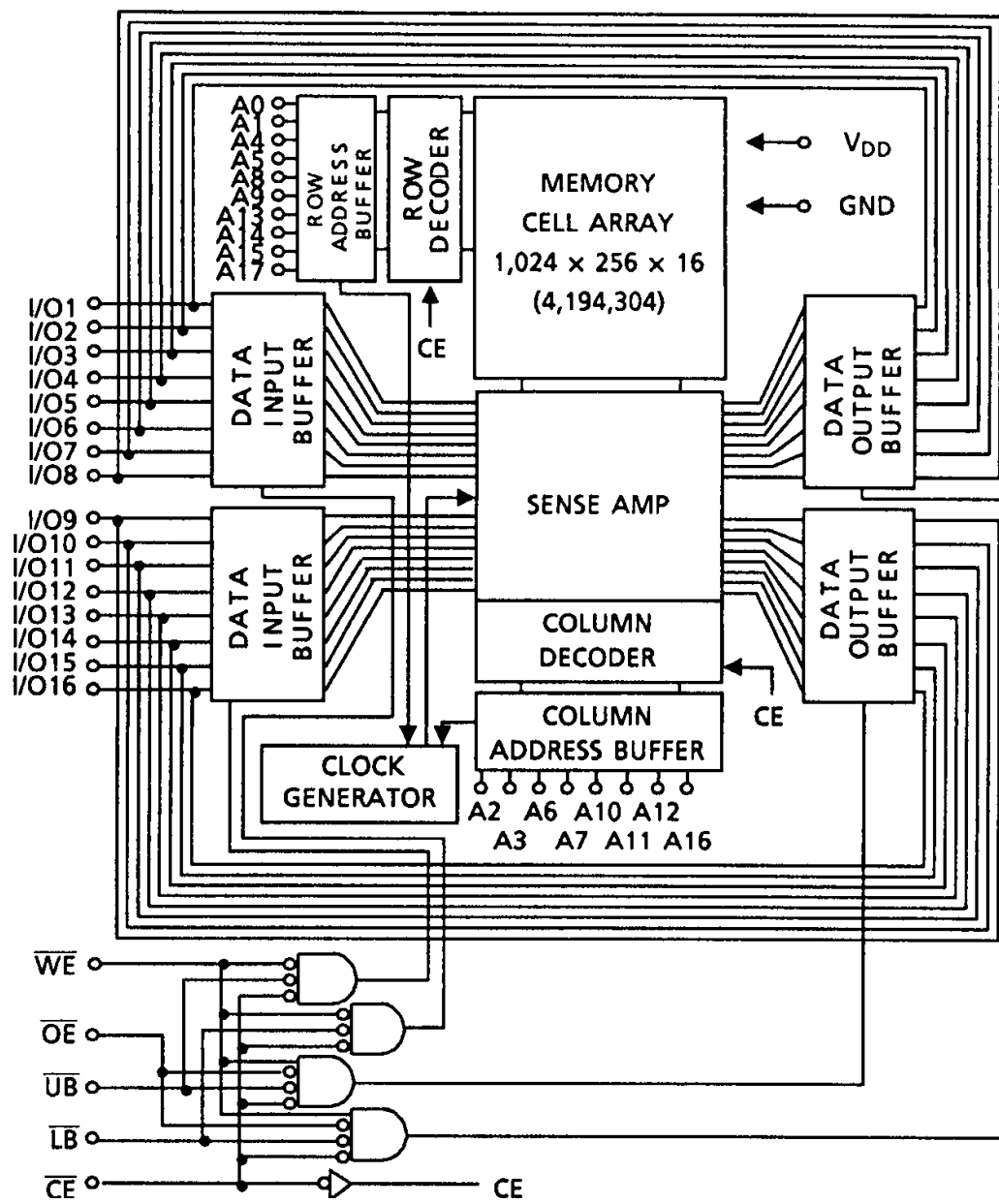


12 or 15 ns access time

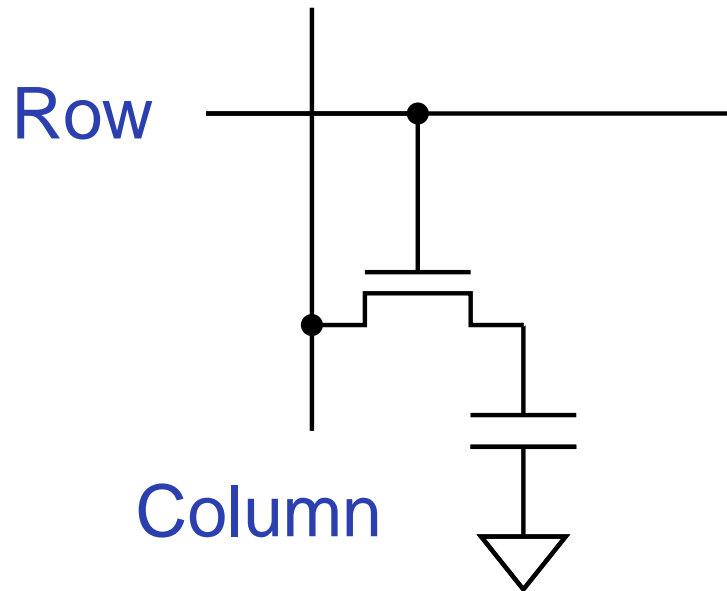
Asynchronous interface

\overline{UB} , \overline{LB} select bytes

Toshiba TC55V16256J 256K × 16



Dynamic RAM Cell

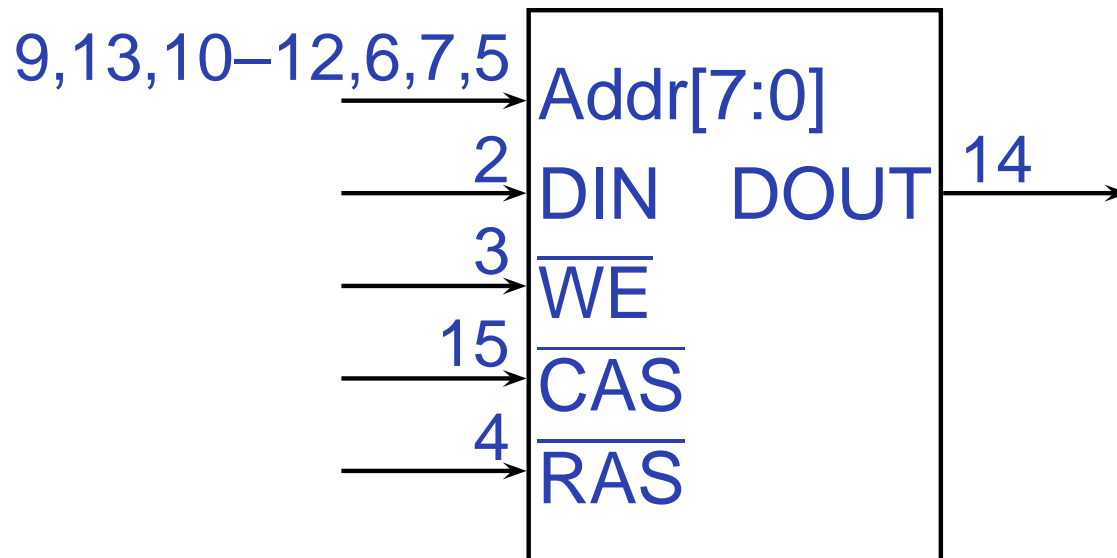


Basic problem: Leakage

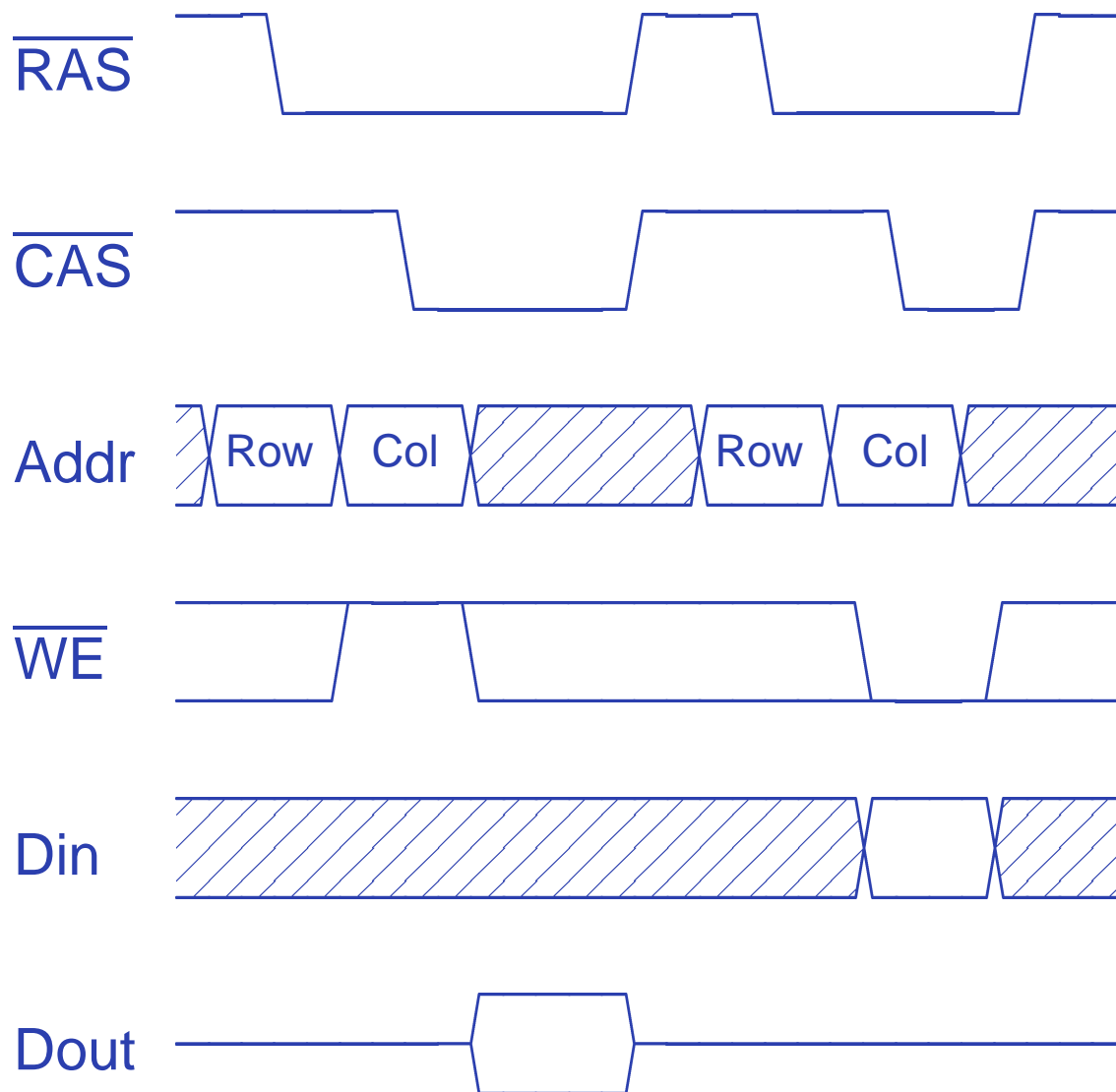
Solution: Refresh

Ancient DRAM: 4164

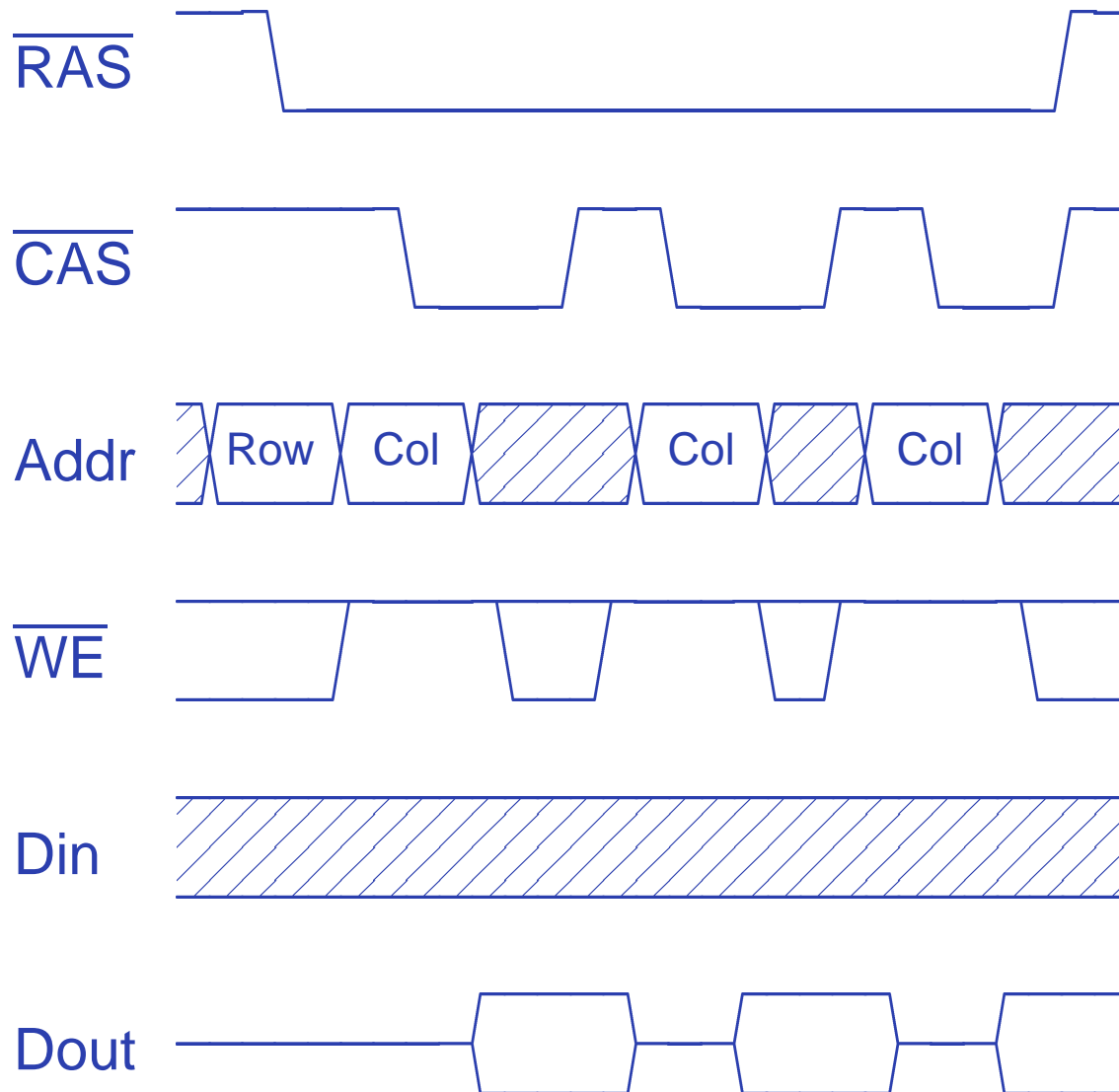
64K × 1
Apple IIe vintage



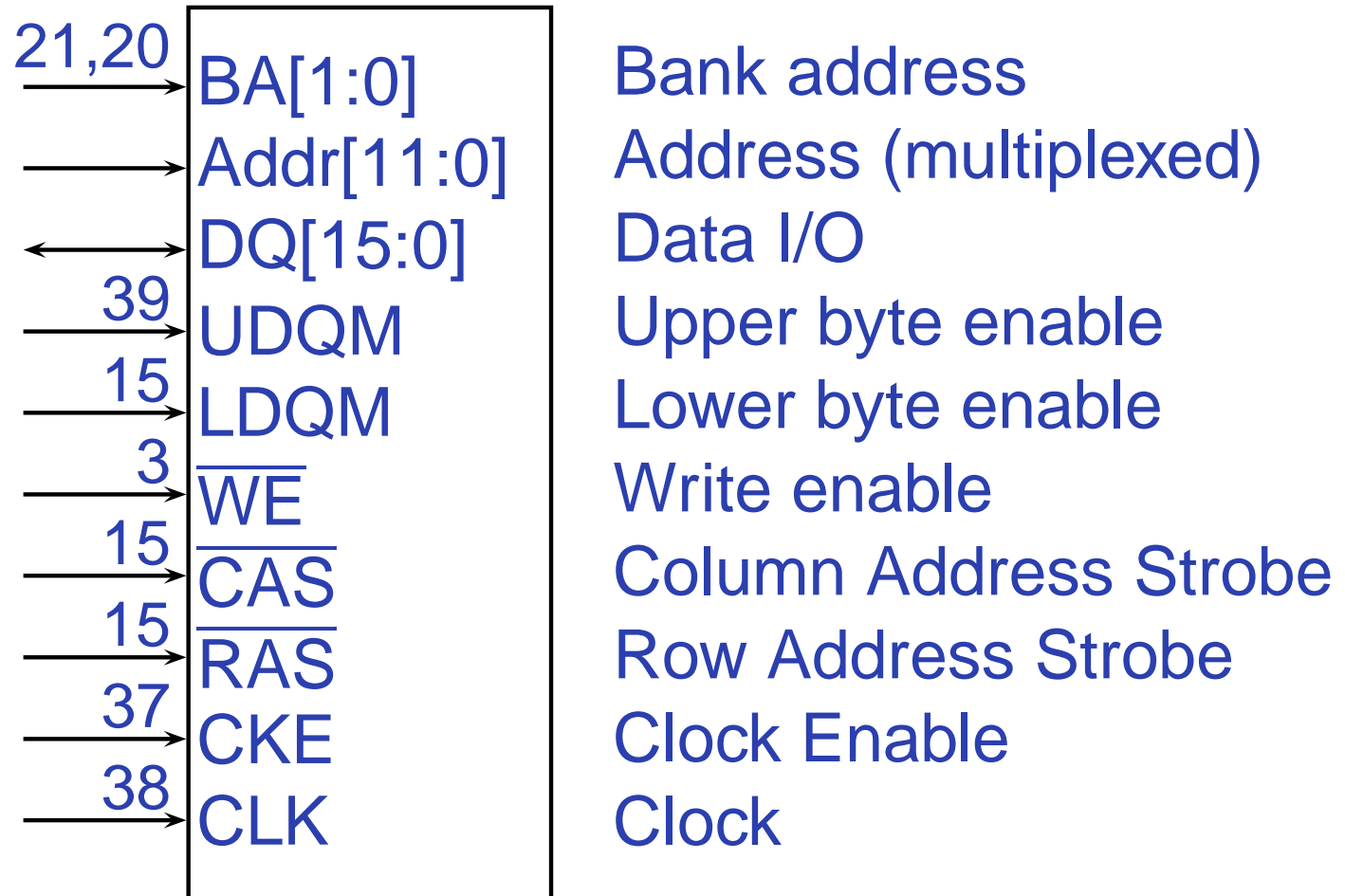
Basic DRAM read and write cycles



Page mode read cycle



Samsung 8M × 16 SDRAM

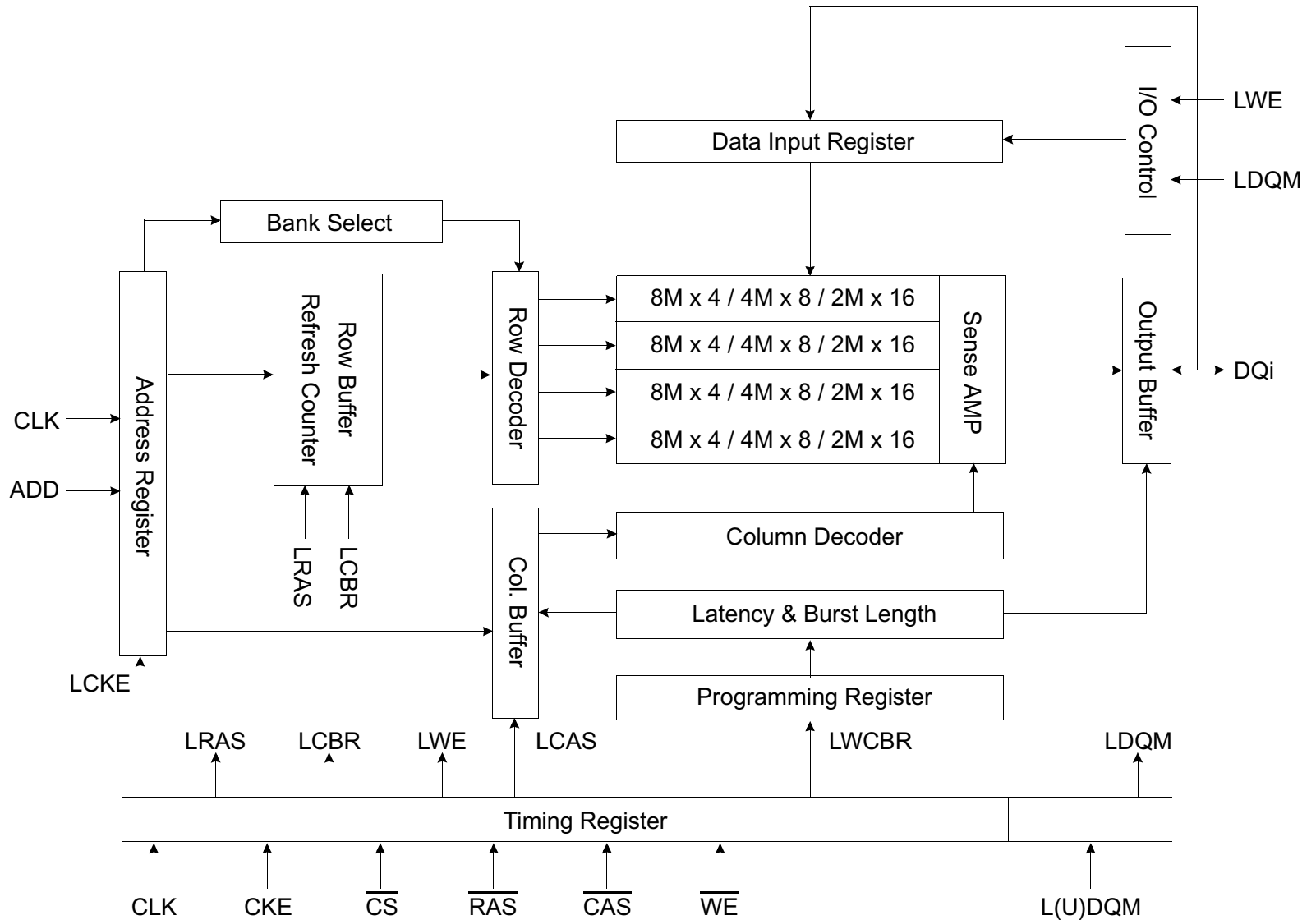


Synchronous interface

Designed for burst-mode operation

Four separate banks; pipelined operation

Samsung 8M × 16 SDRAM



SDRAM: Control Signals

$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{WE}}$	action
1	1	1	NOP
0	0	0	Load mode register
0	1	1	Active (select row)
1	0	1	Read (select column, start burst)
1	0	0	Write (select column, start burst)
1	1	0	Terminate Burst
0	1	0	Precharge (deselect row)
0	0	1	Auto Refresh

Mode register: selects 1/2/4/8-word bursts, CAS latency, burst on write

SDRAM: Timing with 2-word bursts

